

Silicon wafer

Product name	Diameter (in)	Type	Resistivity ($\Omega \cdot \text{cm}$)
① CZ, MCZ wrapped wafer	3~8	N&P	1~300
② FZ wafer (NTD)	3~6	N&P	30~800
③ Si epitaxial wafers	4~8	N&P	Blanket: 0.03~200, Buried Layer: 0.5~200
④ SiC, GaN epitaxial wafers	4~6	N&P	
⑤ Foundry Service	Power IC : Discrete (5 to 6 in), Sic (4 in), GaN (6 in) etc.		

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